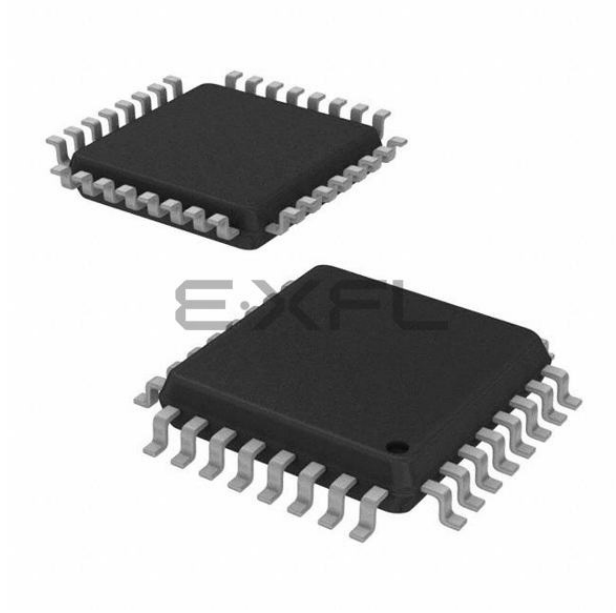

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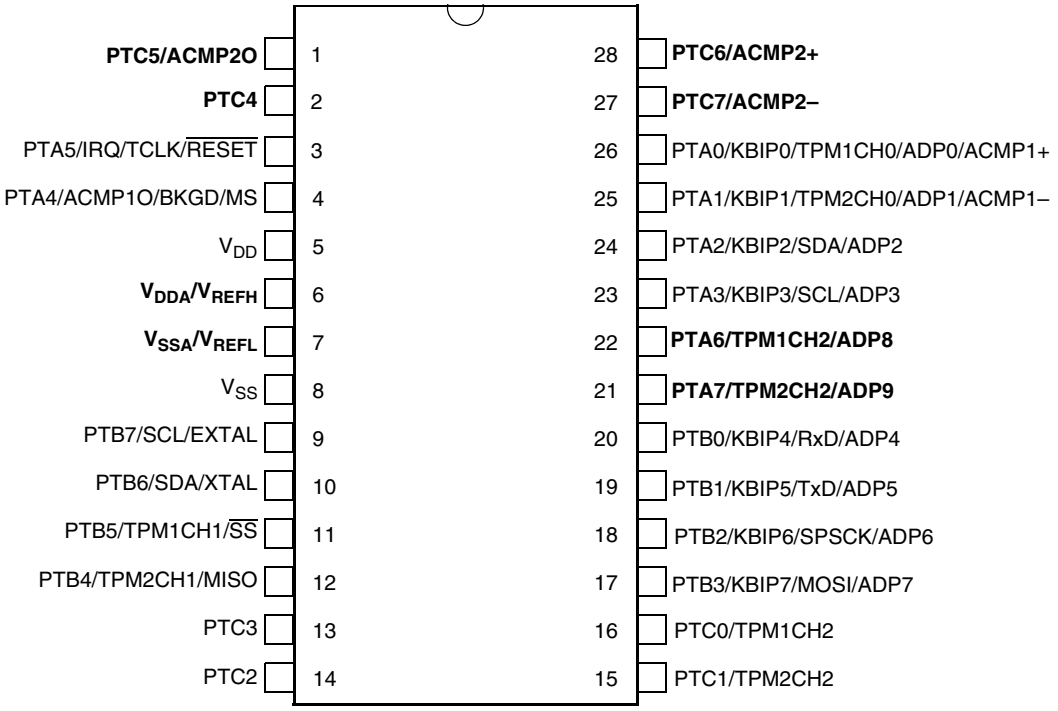
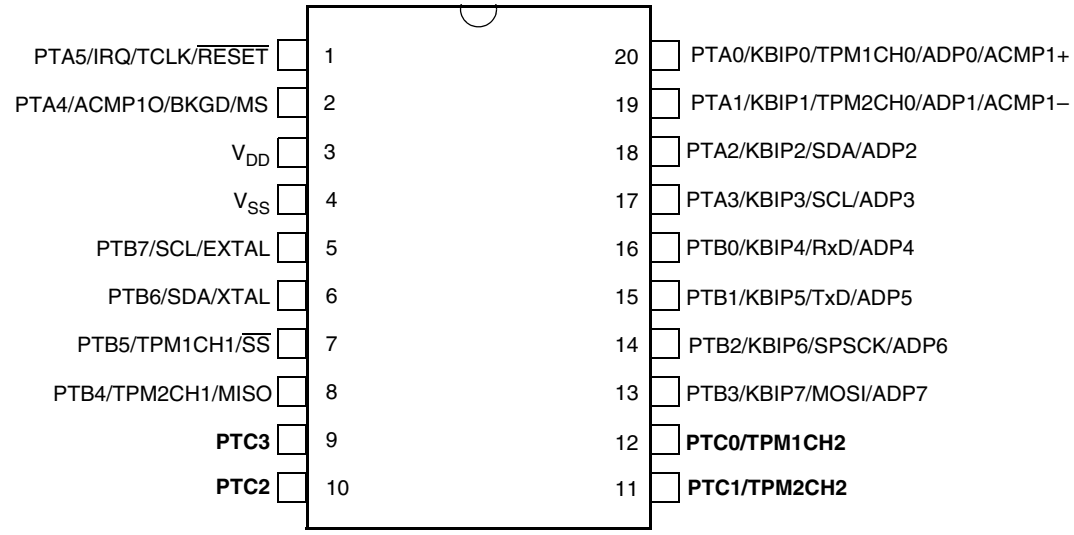
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SCI, SPI
Peripherals	LVD, PWM, WDT
Number of I/O	26
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256 x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s08qe4clcr



Pins shown in bold type are lost in the next lower pin count package.

Figure 3. MC9S08QE8 Series in 28-pin SOIC Package



Pins shown in bold type are lost in the next lower pin count package.

Figure 4. MC9S08QE8 Series in 20-pin SOIC Package

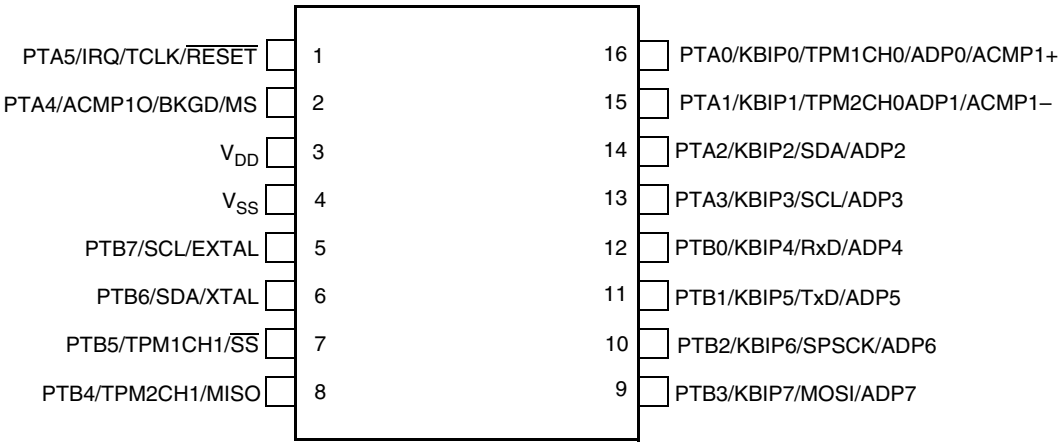


Figure 5. MC9S08QE8 Series in 16-pin PDIP and TSSOP Packages

Table 1. Pin Availability by Package Pin-Count

Pin Number				<-- Lowest **Priority** --> Highest				
32	**28**	**20**	**16**	**Port Pin**	**Alt 1**	**Alt 2**	**Alt 3**	**Alt 4**
1	—	—	—	PTD1				
2	—	—	—	PTD0				
3	5	3	3					V_{DD}
4	6	—	—					V_{DDA}/V_{REFH}
5	7	—	—					V_{SSA}/V_{REFL}
6	8	4	4					V_{SS}
7	9	5	5	PTB7	SCL[1]			EXTAL
8	10	6	6	PTB6	SDA[1]			XTAL
9	11	7	7	PTB5	TPM1CH1	$\overline{SS}$		
10	12	8	8	PTB4	TPM2CH1	MISO		
11	13	9	—	PTC3				
12	14	10	—	PTC2				
13	15	11	—	PTC1	TPM2CH2[2]			
14	16	12	—	PTC0	TPM1CH2[3]			
15	17	13	9	PTB3	KBIP7	MOSI	ADP7	
16	18	14	10	PTB2	KBIP6	SPSCK	ADP6	
17	19	15	11	PTB1	KBIP5	TxD	ADP5	
18	20	16	12	PTB0	KBIP4	RxD	ADP4	
19	21	—	—	PTA7	TPM2CH2[2]		ADP9	
20	22	—	—	PTA6	TPM1CH2[3]		ADP8	
21	—	—	—	PTD3				
22	—	—	—	PTD2				
23	23	17	13	PTA3	KBIP3	SCL[1]	ADP3	
24	24	18	14	PTA2	KBIP2	SDA[1]	ADP2	
25	25	19	15	PTA1	KBIP1	TPM2CH0	ADP1[4]	ACMP1–[4]

3.3 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 3 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}) or the programmable pullup resistor associated with the pin is enabled.

Table 3. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	–0.3 to 3.8	V
Maximum current into V_{DD}	I_{DD}	120	mA
Digital input voltage	V_{In}	–0.3 to V_{DD} + 0.3	V
Instantaneous maximum current Single pin limit (applies to all port pins)[1, 2, 3]	I_D	±25	mA
Storage temperature range	T_{stg}	–55 to 150	°C

1 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

2 All functional non-supply pins, except for PTA5 are internally clamped to V_{SS} and V_{DD}.

3 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low (which would reduce overall power consumption).

3.4 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 4. Thermal Characteristics

Rating	Symbol	Value	Unit
Operating temperature range (packaged)	T_A	T_L to T_H –40 to 85	°C
Maximum junction temperature	T_{JM}	95	°C
Thermal resistance Single-layer board			
32-pin QFN	θ_{JA}	110	°C/W
32-pin LQFP		66	
28-pin SOIC		57	
20-pin SOIC		71	
16-pin PDIP		64	
16-pin TSSOP		108	
Thermal resistance Four-layer board			
32-pin QFN	θ_{JA}	42	°C/W
32-pin LQFP		47	
28-pin SOIC		42	
20-pin SOIC		52	
16-pin PDIP		47	
16-pin TSSOP		78	

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \qquad \textit{Eqn. 1}$$

where:

T_A = Ambient temperature, °C
θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W
$P_D = P_{int} + P_{I/O}$
$P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power
$P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273\ °C) \qquad \textit{Eqn. 2}$$

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273\ °C) + \theta_{JA} \times (P_D)^2 \qquad \textit{Eqn. 3}$$

where K is a constant pertaining to the particular part. K can be determined from equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving Equation 1 and Equation 2 iteratively for any value of T_A.

3.5 ESD Protection and Latch-Up Immunity

Although damage from electrostatic discharge (ESD) is much less common on these devices than on early CMOS circuits, normal handling precautions must be taken to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits. During the device qualification, ESD stresses were performed for the human body model (HBM), the machine model (MM) and the charge device model (CDM).

A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless instructed otherwise in the device specification.

Table 5. ESD and Latch-up Test Conditions

Model	Description	Symbol	Value	Unit
Human Body	Series resistance	R1	1500	Ω
	Storage capacitance	C	100	pF
	Number of pulses per pin	—	3	—
Machine	Series resistance	R1	0	Ω
	Storage capacitance	C	200	pF
	Number of pulses per pin	—	3	—
Latch-up	Minimum input voltage limit	—	–2.5	V
	Maximum input voltage limit	—	7.5	V

Table 6. ESD and Latch-Up Protection Characteristics

No.	Rating[1]	Symbol	Min	Max	Unit
1	Human body model (HBM)	V_{HBM}	±2000	—	V
2	Machine model (MM)	V_{MM}	±200	—	V
3	Charge device model (CDM)	V_{CDM}	±500	—	V
4	Latch-up current at T_A = 85 °C	I_{LAT}	±100	—	mA

1 Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

3.6 DC Characteristics

This section includes information about power supply requirements and I/O pin characteristics.

Table 7. DC Characteristics

Num	C	Characteristic		Symbol	Condition	Min.	Typical[1]	Max.	Unit
1		Operating voltage V_{DD} rising V_{DD} falling				2.0[2] 1.8		3.6	V
2	C	Output high voltage	All I/O pins, low-drive strength	V_{OH}	V_{DD} > 1.8 V, I_{Load} = –2 mA	V_{DD} – 0.5	—	—	V
	P		All I/O pins, high-drive strength		V_{DD} > 2.7 V, I_{Load} = –10 mA	V_{DD} – 0.5	—	—	
	C				V_{DD} > 1.8V, I_{Load} = –2 mA	V_{DD} – 0.5	—	—	
3	D	Output high current	Max total I_{OH} for all ports	I_{OHT}	—	—	—	100	mA
4	C	Output low voltage	All I/O pins, low-drive strength	V_{OL}	V_{DD} > 1.8 V, I_{Load} = 0.6 mA	—	—	0.5	V
	P		All I/O pins, high-drive strength		V_{DD} > 2.7 V, I_{Load} = 10 mA	—	—	0.5	
	C				V_{DD} > 1.8 V, I_{Load} = 3 mA	—	—	0.5	
5	D	Output low current	Max total I_{OL} for all ports	I_{OLT}	—	—	—	100	mA
6	P	Input high voltage	All digital inputs	V_{IH}	V_{DD} > 2.7 V	0.70 × V_{DD}	—	—	V
	C				V_{DD} > 1.8 V	0.85 × V_{DD}	—	—	
7	P	Input low voltage	All digital inputs	V_{IL}	V_{DD} > 2.7 V	—	—	0.35 × V_{DD}	
	C				V_{DD} > 1.8 V	—	—	0.30 × V_{DD}	
8	C	Input hysteresis	All digital inputs	V_{hys}	—	0.06 x V_{DD}	—	—	mV
9	P	Input leakage current	All input only pins (per pin)	$\lvert I_{In} \rvert$	V_{In} = V_{DD} or V_{SS}	—	—	1	µA
10	P	Hi-Z (off-state) leakage current	All input/output (per pin)	$\lvert I_{OZ} \rvert$	V_{In} = V_{DD} or V_{SS}	—	—	1	µA
11	P	Total leakage combined for all inputs and Hi-Z pins	All input only and I/O	$\lvert I_{OZTOT} \rvert$	V_{In} = V_{DD} or V_{SS}	—	—	2	µA
12a	P	Pullup, pulldown resistors	All digital inputs, when enabled (all I/O pins other than PTA5/IRQ/TCLK/$\overline{\text{RESET}}$)	R_{PU}, R_{PD}	—	17.5	—	52.5	kΩ

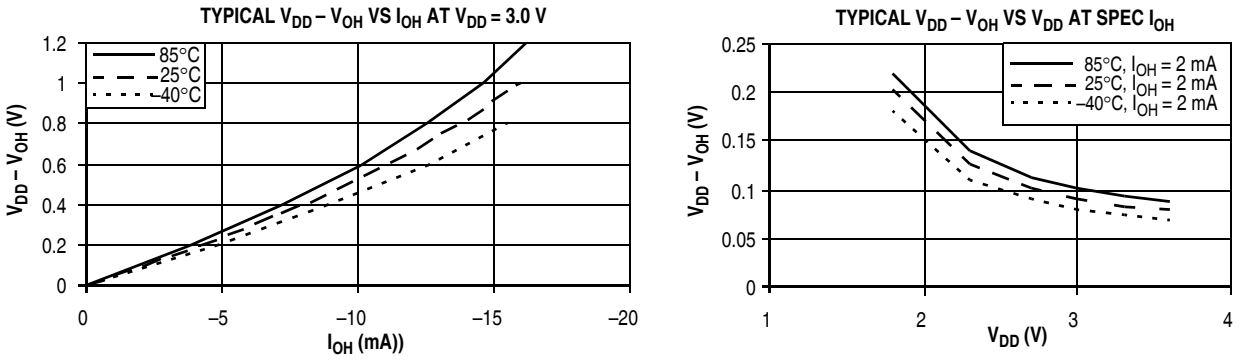


Figure 9. Typical High-Side (Source) Characteristics — Low Drive (PTxDSn = 0)

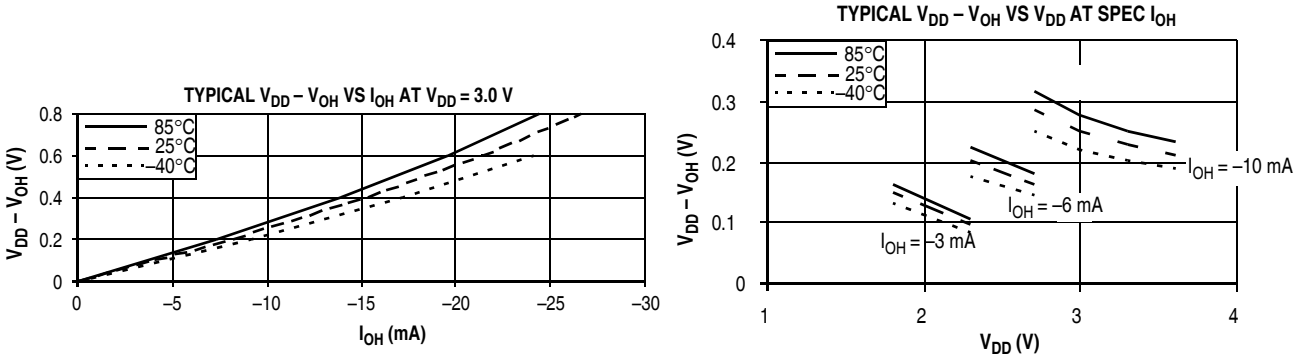


Figure 10. Typical High-Side (Source) Characteristics — High Drive (PTxDSn = 1)

3.7 Supply Current Characteristics

This section includes information about power supply current in various operating modes.

Table 8. Supply Current Characteristics

Num	C	Parameter	Symbol	Bus Freq	V_{DD} (V)	Typical[1]	Max	Unit	Temp (°C)
1	P	Run supply current FEI mode, all modules on	RI_{DD}	10 MHz	3	5.60	8.2	mA	–40 to 85 °C
	T			1 MHz		0.80	—		
2	T	Run supply current FEI mode, all modules off	RI_{DD}	10 MHz	3	3.60	—	mA	–40 to 85 °C
	T			1 MHz		0.51	—		
3	T	Run supply current LPRS = 0, all modules off	RI_{DD}	16 kHz FBILP	3	165	—	µA	–40 to 85 °C
	T			16 kHz FBELP		105	—		
4	T	Run supply current LPRS = 1, all modules off; running from flash	RI_{DD}	16 kHz FBILP	3	77	—	µA	–40 to 85 °C
	T			16 kHz FBELP		21	—		

Table 8. Supply Current Characteristics (continued)

Num	C	Parameter	Symbol	Bus Freq	V_{DD} (V)	Typical[1]	Max	Unit	Temp (°C)
5	T	Run supply current LPRS = 1, all modules off; running from RAM	RI_{DD}	16 kHz FBILP	3	77	—	µA	–40 to 85 °C
	T			16 kHz FBELP		7.3	—		
6	T	Wait mode supply current FEI mode, all modules off	WI_{DD}	10 MHz	3	570	—	µA	–40 to 85 °C
	T			1 MHz		290	—		
7	T	Wait mode supply current LPRS = 1, all modules off	WI_{DD}	16 kHz FBELP	3	1	—	µA	–40 to 85 °C
8	P	Stop2 mode supply current	$S2I_{DD}$	—	3	0.3	0.65	µA	–40 to 25 °C
	C			—		0.5	0.8		70 °C
	P			—		1	2.5		85 °C
	C			—	2	0.25	0.50		–40 to 25 °C
	C			—		0.3	0.6		70 °C
	C			—		0.7	2.0		85 °C
9	P	Stop3 mode supply current no clocks active	$S3I_{DD}$	—	3	0.4	0.8	µA	–40 to 25 °C
	C			—		1.0	1.8		70 °C
	P			—		3	6		85 °C
	C			—	2	0.35	0.60		–40 to 25 °C
	C			—		0.8	1.5		70 °C
	C			—		2.5	5.5		85 °C

1 Data in Typical column was characterized at 3.0 V, 25°C or is typical recommended value.

Table 9. Stop Mode Adders

Num	C	Parameter	Condition	Temperature				Units
				–40°C	25°C	70°C	85°C	
1	T	LPO	—	50	75	100	150	nA
2	T	ERREFSTEN	RANGE = HGO = 0	1000	1000	1100	1500	nA
3	T	IREFSTEN[1]	—	63	70	77	81	µA
4	T	RTC	Does not include clock source current	50	75	100	150	nA
5	T	LVD[1]	LVDSE = 1	90	100	110	115	µA
6	T	ACMP[1]	Not using the bandgap (BGBE = 0)	18	20	22	23	µA
7	T	ADC[1]	ADLPC = ADLSMP = 1 Not using the bandgap (BGBE = 0)	95	106	114	120	µA

1 Not available in stop2 mode.

3.8 External Oscillator (XOSCVLP) Characteristics

Refer to Figure 12 and Figure 13 for crystal or resonator circuits.

Table 10. XOSCVLP Specifications (Temperature Range = –40 to 85°C Ambient)

Num	C	Characteristic	Symbol	Min.	Typical[1]	Max.	Unit
1	C	Oscillator crystal or resonator (EREFS = 1, ERCLKEN = 1) Low range (RANGE = 0) High range (RANGE = 1), high gain (HGO = 1), FBELP mode High range (RANGE = 1), low power (HGO = 0), FBELP mode	 f_{lo} f_{hi} f_{hi}	 32 1 1	 — — —	 38.4 16 8	 kHz MHz MHz
2	D	Load capacitors Low range (RANGE=0), low power (HGO = 0) Other oscillator settings	C_1,C_2	See Note [2] See Note [3]			
3	D	Feedback resistor Low range, low power (RANGE = 0, HGO = 0)[2] Low range, high gain (RANGE = 0, HGO = 1) High range (RANGE = 1, HGO = X)	R_F	 — — —	 — 10 1	 — — —	MΩ
4	D	Series resistor — Low range, low power (RANGE = 0, HGO = 0)[2] Low range, high gain (RANGE = 0, HGO = 1) High range, low power (RANGE = 1, HGO = 0) High range, high gain (RANGE = 1, HGO = 1) ≥ 8 MHz 4 MHz 1 MHz	R_S	 — — — — — —	 — 100 0 0 0 0	 — — — 0 10 20	kΩ
5	C	Crystal start-up time[4] Low range, low power Low range, high gain High range, low power High range, high gain	 t_{CSTL} t_{CSTH} 	 — — — —	 600 400 5 15	 — — — —	ms
6	D	Square wave input clock frequency (EREFS = 0, ERCLKEN = 1) FEE mode FBE or FBELP mode	f_{extal}	0.03125 0	— —	20 20	MHz MHz

1 Data in Typical column was characterized at 3.0 V, 25 °C or is typical recommended value.

2 Load capacitors (C_1,C_2), feedback resistor (R_F) and series resistor (R_S) are incorporated internally when RANGE = HGO = 0.

3 See crystal or resonator manufacturer's recommendation.

4 Proper PC board layout procedures must be followed to achieve specifications.

Table 11. ICS Frequency Specifications (Temperature Range = –40 to 85°C Ambient) (continued)

Num	C	Characteristic	Symbol	Min.	Typical[1]	Max.	Unit
7	C	Resolution of trimmed DCO output frequency at fixed voltage and temperature (not using FTRIM)	$\Delta f_{dco\_res\_t}$	—	± 0.2	± 0.4	$\%f_{dco}$
8	C	Total deviation of DCO output from trimmed frequency[3] Over full voltage and temperature range Over fixed voltage and temperature range of 0 to 70 °C	Δf_{dco_t}	—	–1.0 to 0.5 ±0.5	± 2 ± 1	$\%f_{dco}$
10	C	FLL acquisition time[4]	$t_{Acquire}$	—	—	1	ms
11	C	Long term jitter of DCO output clock (averaged over 2-ms interval)[5]	C_{Jitter}	—	0.02	0.2	$\%f_{dco}$

1 Data in Typical column was characterized at 3.0 V, 25 °C or is typical recommended value.

2 The resulting bus clock frequency should not exceed the maximum specified bus clock frequency of the device.

3 This parameter is characterized and not tested on each device.

4 This specification applies to any time the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (FBELP, FBILP) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

5 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{Bus}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

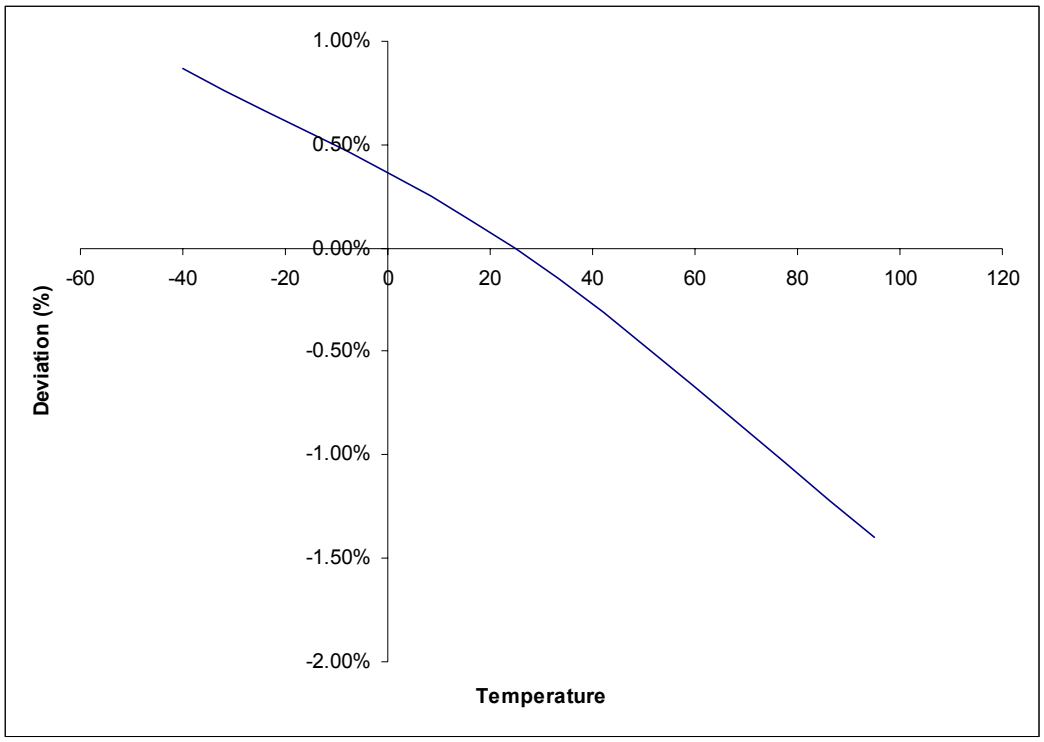


Figure 14. Deviation of DCO Output from Trimmed Frequency (20 MHz, 3.0 V)

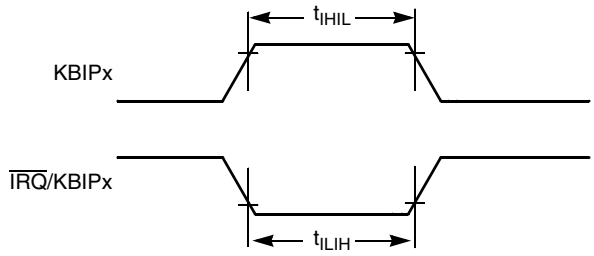


Figure 16. IRQ/KBIPx Timing

3.10.2 TPM Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 13. TPM Input Timing

No.	C	Function	Symbol	Min	Max	Unit
1	D	External clock frequency	f_{TCLK}	0	$f_{Bus}/4$	Hz
2	D	External clock period	t_{TCLK}	4	—	t_{cyc}
3	D	External clock high time	t_{clkh}	1.5	—	t_{cyc}
4	D	External clock low time	t_{clkl}	1.5	—	t_{cyc}
5	D	Input capture pulse width	t_{ICPW}	1.5	—	t_{cyc}

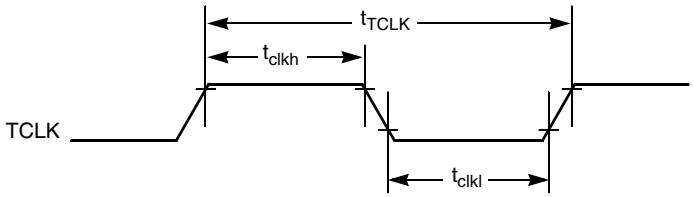


Figure 17. Timer External Clock

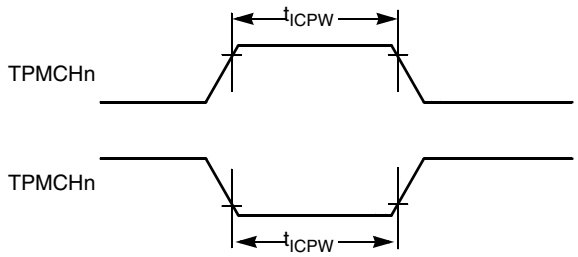
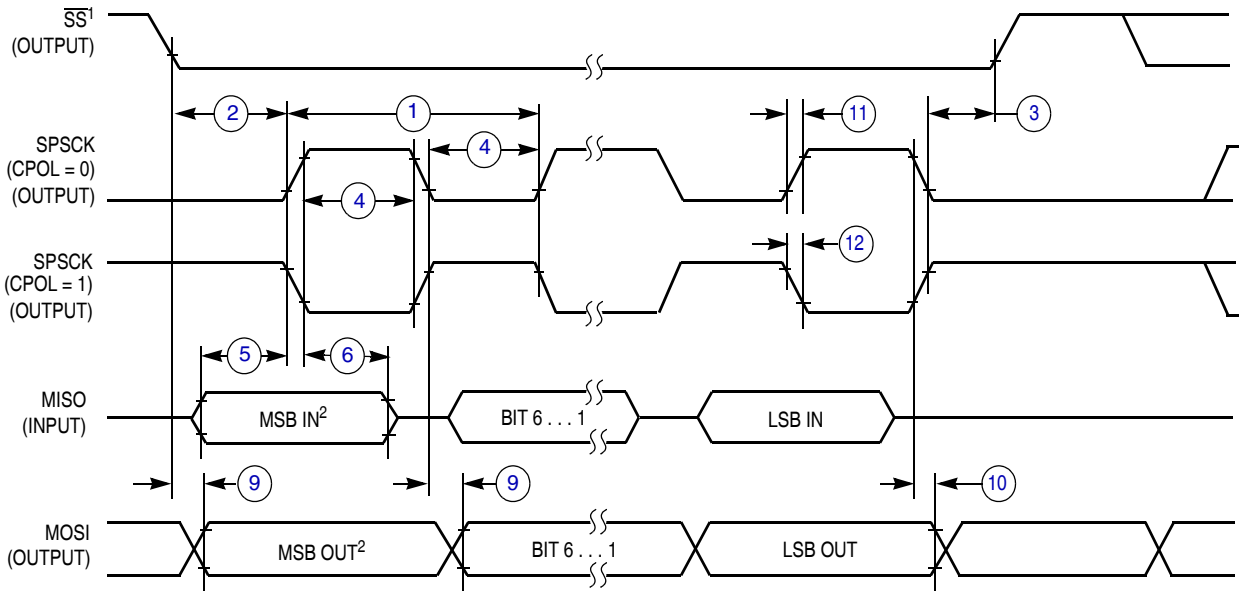


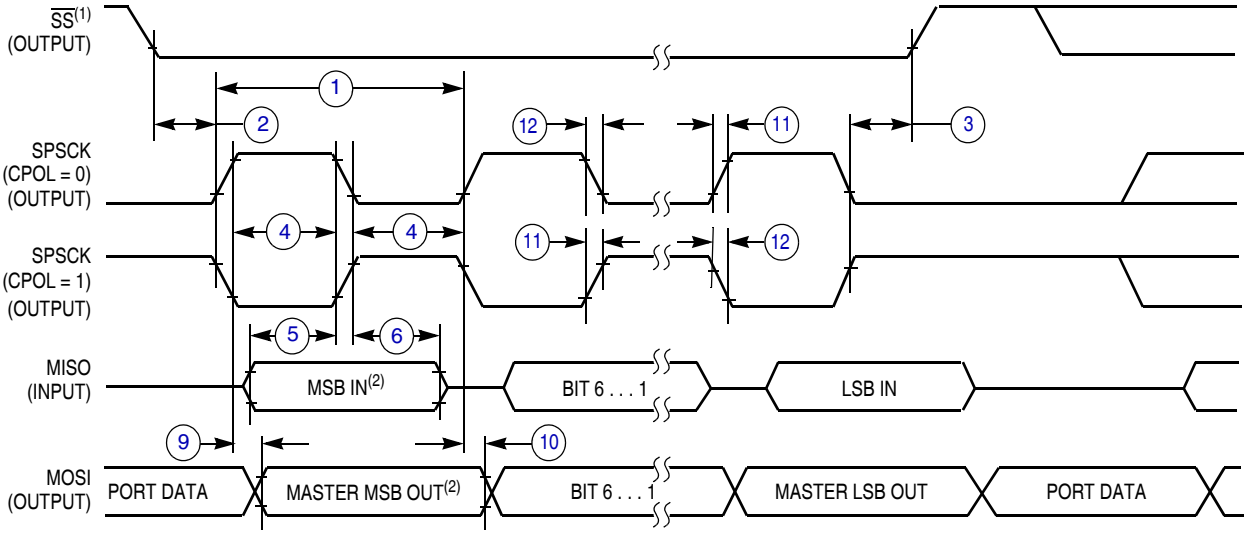
Figure 18. Timer Input Capture Pulse



NOTES:

1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 19. SPI Master Timing (CPHA = 0)



NOTES:

1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 20. SPI Master Timing (CPHA =1)

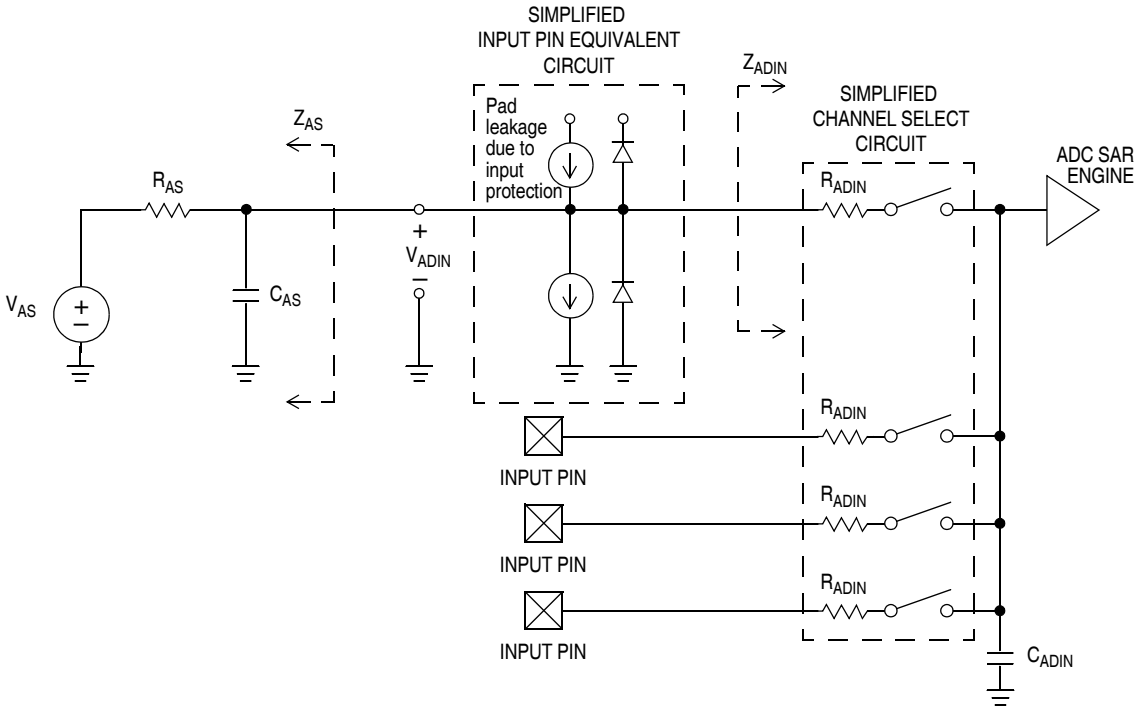


Figure 23. ADC Input Impedance Equivalency Diagram

Table 17. ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA})

C	Characteristic	Conditions	Symbol	Min	Typ[1]	Max	Unit	Comment
T	Supply current ADLPC = 1 ADLSMP = 1 ADCO = 1		I_{DDA}	—	120	—	μA	
T	Supply current ADLPC = 1 ADLSMP = 0 ADCO = 1		I_{DDA}	—	202	—	μA	
T	Supply current ADLPC = 0 ADLSMP = 1 ADCO = 1		I_{DDA}	—	288	—	μA	
P	Supply current ADLPC = 0 ADLSMP = 0 ADCO = 1		I_{DDA}	—	0.532	1	mA	
P	ADC asynchronous clock source	High speed (ADLPC = 0)	f_{ADACK}	2	3.3	5	MHz	t_{ADACK} = $1/f_{ADACK}$
		Low power (ADLPC = 1)		1.25	2	3.3		

Table 17. ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) (continued)

C	Characteristic	Conditions	Symbol	Min	Typ[1]	Max	Unit	Comment
P	Conversion time (including sample time)	Short sample (ADLSMP = 0)	t_{ADC}	—	20	—	ADCK cycles	See QE8 reference manual for conversion time variances
		Long sample (ADLSMP = 1)		—	40	—		
P	Sample time	Short sample (ADLSMP = 0)	t_{ADS}	—	3.5	—	ADCK cycles	
		Long sample (ADLSMP = 1)		—	23.5	—		
D	Temp sensor slope	–40 °C– 25 °C	m	—	1.646	—	mV/°C	
		25 °C– 85 °C		—	1.769	—		
D	Temp sensor voltage	25 °C	V_{TEMP25}	—	701.2	—	mV	
Characteristics for devices with dedicated analog supply (28- and 32-pin packages only)								
T	Total unadjusted error	12-bit mode, 3.6> V_{DDA} > 2.7	E_{TUE}	—	–1 to 3	–2.5 to 5.5	LSB[2]	Includes quantization
T		12-bit mode, 2.7> V_{DDA} > 1.8V		—	–1 to 3	–3.0 to 6.5		
P		10-bit mode		—	±1	±2.5		
P		8-bit mode		—	±0.5	±1.0		
T	Differential non-linearity	12-bit mode	DNL	—	±1.0	–1.5 to 2.0	LSB[2]	
P		10-bit mode[3]		—	±0.5	±1.0		
P		8-bit mode[3]		—	±0.3	±0.5		
T	Integral non-linearity	12-bit mode	INL	—	±1.5	–2.5 to 2.75	LSB[2]	
T		10-bit mode		—	±0.5	±1.0		
T		8-bit mode		—	±0.3	±0.5		
T	Zero-scale error	12-bit mode	E_{ZS}	—	±1.5	±2.5	LSB[2]	V_{ADIN} = V_{SSA}
P		10-bit mode		—	±0.5	±1.5		
P		8-bit mode		—	±0.5	±0.5		
T	Full-scale error	12-bit mode	E_{FS}	—	±1.0	–3.5 to 1.0	LSB[2]	V_{ADIN} = V_{DDA}
P		10-bit mode		—	±0.5	±1		
P		8-bit mode		—	±0.5	±0.5		
D	Quantization error	12-bit mode	E_Q	—	–1 to 0	—	LSB[2]	
		10-bit mode		—	—	±0.5		
		8-bit mode		—	—	±0.5		

Table 17. ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) (continued)

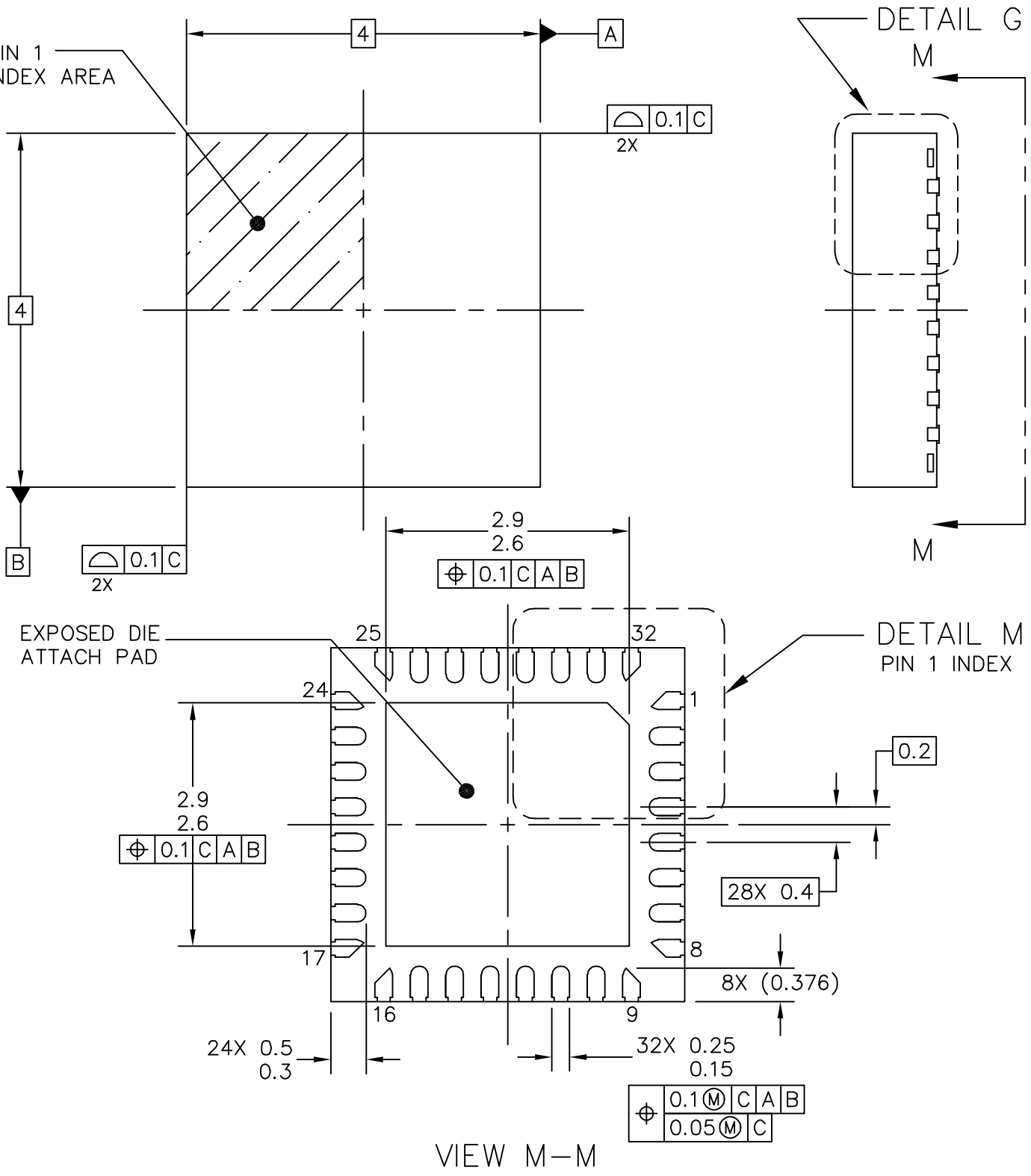
C	Characteristic	Conditions	Symbol	Min	Typ[1]	Max	Unit	Comment
D	Input leakage error	12-bit mode	E_{IL}	—	±2	—	LSB[2]	Pad leakage[4] * R_{AS}
		10-bit mode		—	±0.2	±4		
		8-bit mode		—	±0.1	±1.2		
Characteristics for devices with shared supply (16- and 20-pin packages only)								
T	Total unadjusted error	12-bit mode	E_{TUE}	Not recommended usage			LSB[2]	Includes quantization
P		10-bit mode		—	±1.5	±3.5		
P		8-bit mode		—	±0.7	±1.5		
T	Differential non-linearity	12-bit mode	DNL	Not recommended usage			LSB[2]	
P		10-bit mode[3]		—	±0.5	±1.0		
P		8-bit mode[3]		—	±0.3	±0.5		
T	Integral non-linearity	12-bit mode	INL	Not recommended usage			LSB[2]	
T		10-bit mode		—	±0.5	±1.0		
T		8-bit mode		—	±0.3	±0.5		
T	Zero-scale error	12-bit mode	E_{ZS}	Not recommended usage			LSB[2]	V_{ADIN} = V_{SSA}
P		10-bit mode		—	±1.5	±2.1		
P		8-bit mode		—	±0.5	±0.7		
T	Full-scale error	12-bit mode	E_{FS}	Not recommended usage			LSB[2]	V_{ADIN} = V_{DDA}
P		10-bit mode		—	±1	±1.5		
P		8-bit mode		—	±0.5	±0.5		
D	Quantization error	12-bit mode	E_Q	Not recommended usage			LSB[2]	
		10-bit mode		—	—	±0.5		
		8-bit mode		—	—	±0.5		
D	Input leakage error	12-bit mode	E_{IL}	Not recommended usage			LSB[2]	Pad leakage[4] * R_{AS}
		10-bit mode		—	±0.2	±4		
		8-bit mode		—	±0.1	±1.2		

1 Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

2 1 LSB = $(V_{REFH} - V_{REFL})/2^N$

3 Monotonicity and No-missing-codes guaranteed in 10-bit and 8-bit modes

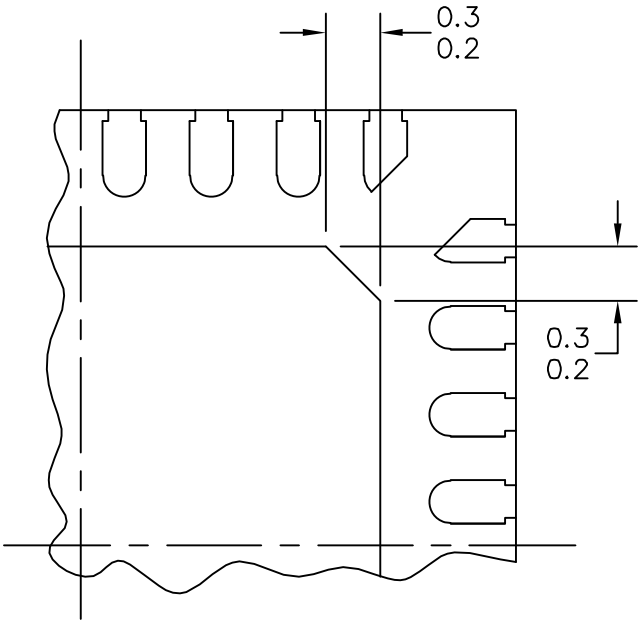
4 Based on input pad leakage current. Refer to pad electricals.



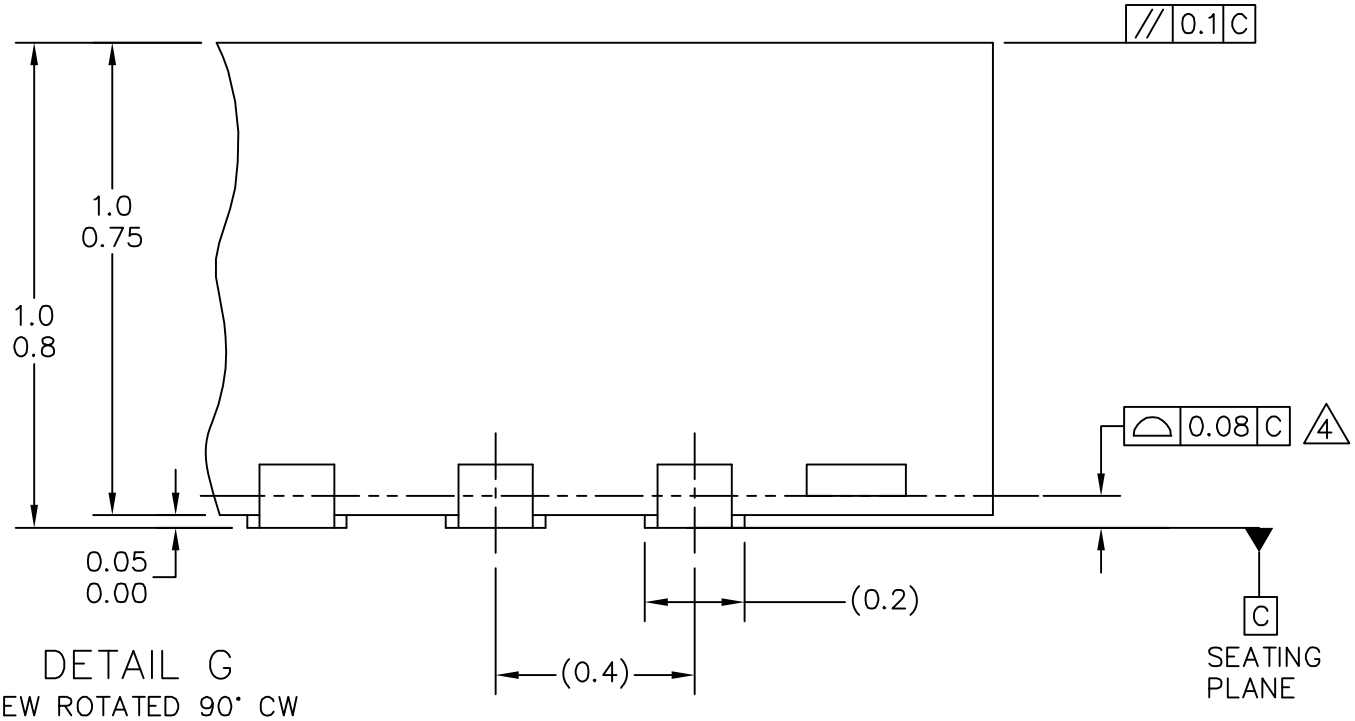
VIEW M–M

MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE

TITLE: THERMALLY ENHANCED QUAD FLAT NON–LEADED PACKAGE (QFN) 32 TERMINAL, 0.4 PITCH (4 X 4 X 1)	DOCUMENT NO: 98ASA00071D	REV: O
	CASE NUMBER: 2078–01	14 APR 2009
	STANDARD: NON–JEDEC	



DETAIL M
PIN 1 BACKSIDE IDENTIFIER



DETAIL G
VIEW ROTATED 90° CW

MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE

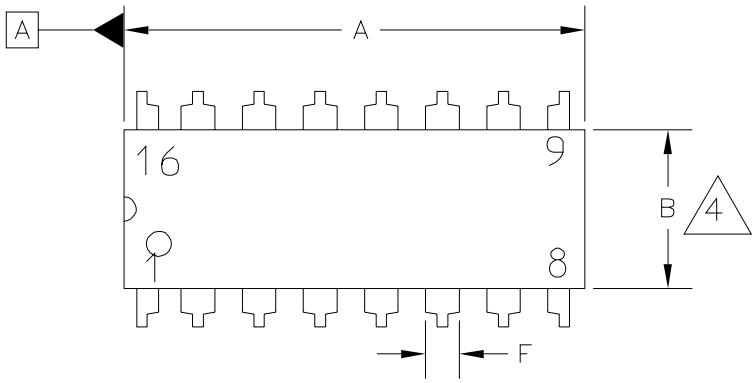
TITLE: THERMALLY ENHANCED QUAD FLAT NON-LEADED PACKAGE (QFN) 32 TERMINAL, 0.4 PITCH (4 X 4 X 1)	DOCUMENT NO: 98ASA00071D	REV: O
	CASE NUMBER: 2078-01	14 APR 2009
	STANDARD: NON-JEDEC	

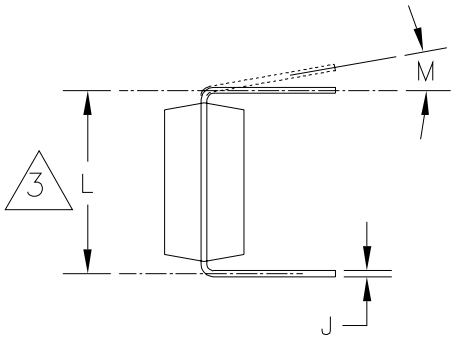
NOTES:

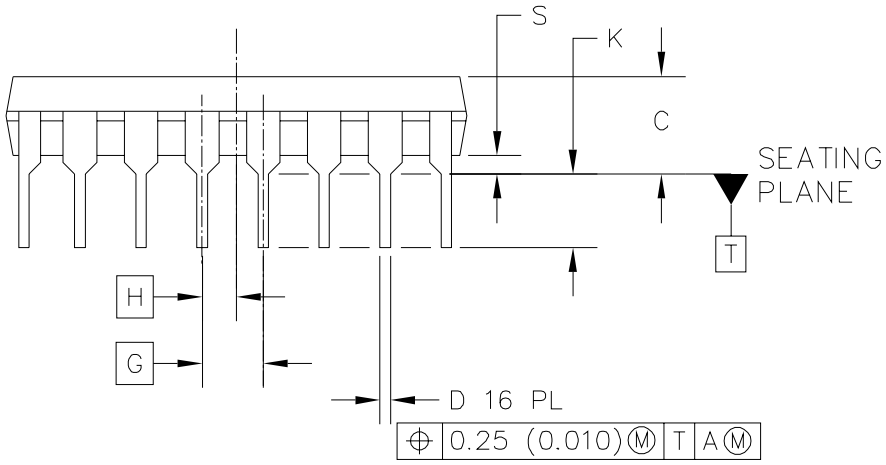
1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994.
3. THE COMPLETE JEDEC DESIGNATOR FOR THIS PACKAGE IS: HF–PQFN.
4. COPLANARITY APPLIES TO LEADS AND DIE ATTACH PAD.
5. MIN. METAL GAP SHOULD BE 0.2MM.

MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE

TITLE: THERMALLY ENHANCED QUAD FLAT NON–LEADED PACKAGE (QFN) 32 TERMINAL, 0.4 PITCH (4 X 4 X 1)	DOCUMENT NO: 98ASA00071D	REV: O
	CASE NUMBER: 2078–01	14 APR 2009
	STANDARD: NON–JEDEC	







MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE

TITLE:	DOCUMENT NO: 98ASB42431B	REV: T
16 LD PDIP	CASE NUMBER: 648-08	19 MAY 2005
	STANDARD: NON-JEDEC	

NOTES:

1. CONTROLLING DIMENSION: MILLIMETER

2. DIMENSIONS AND TOLERANCES PER ANSI Y14.5M-1982.

3. DIMENSION DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE.

4. DIMENSION DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 PER SIDE.

5. DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF THE DIMENSION AT MAXIMUM MATERIAL CONDITION.

6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

7. DIMENSIONS ARE TO BE DETERMINED AT DATUM PLANE -W-.

MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE

TITLE:	DOCUMENT NO: 98ASH70247A	REV: B
16 LD TSSOP, PITCH 0.65MM	CASE NUMBER: 948F-01	19 MAY 2005
	STANDARD: JEDEC	